

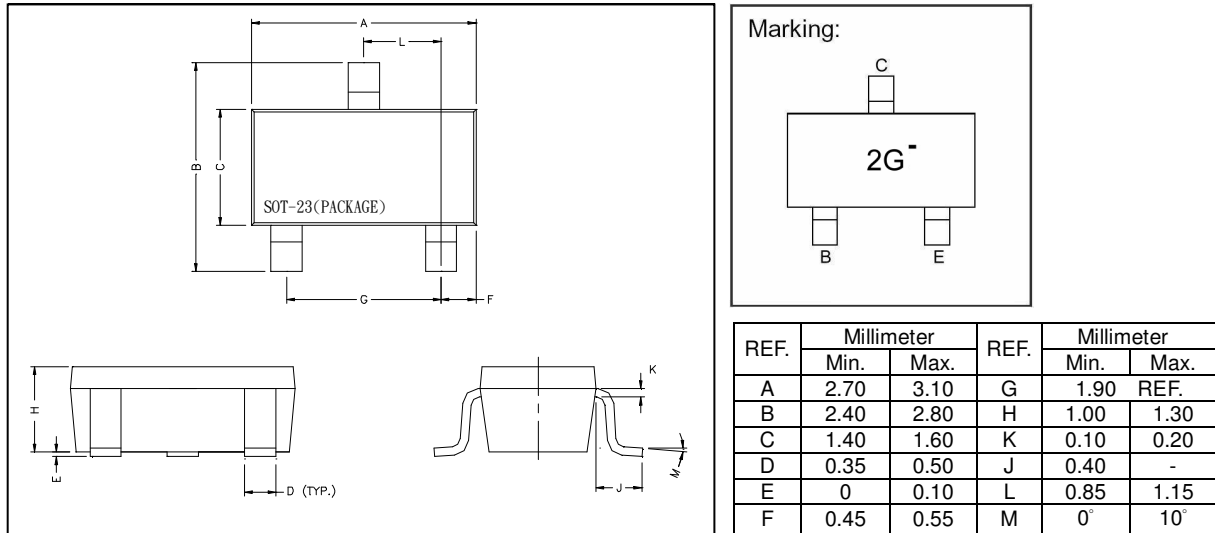
GMBTA56

PNP SILICON TRANSISTOR

Description

The GMBTA56 is amplifier applications.

Package Dimensions



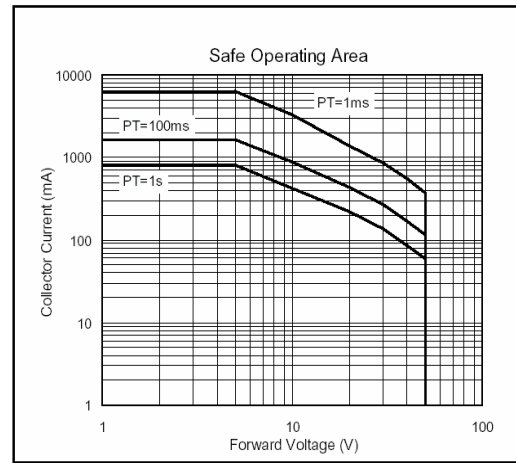
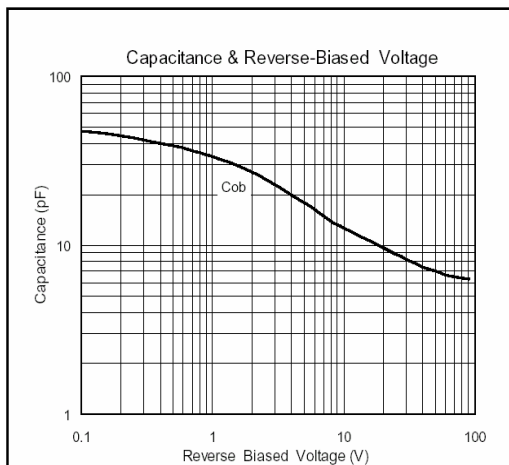
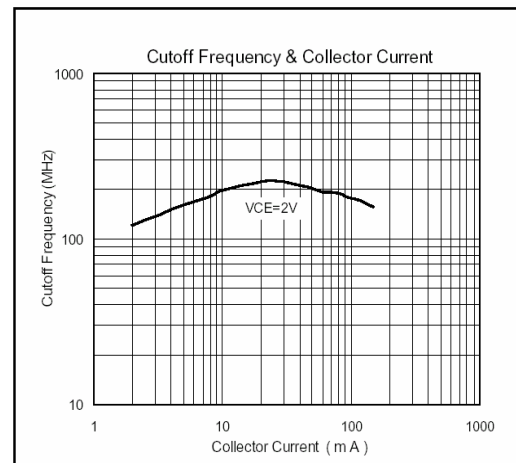
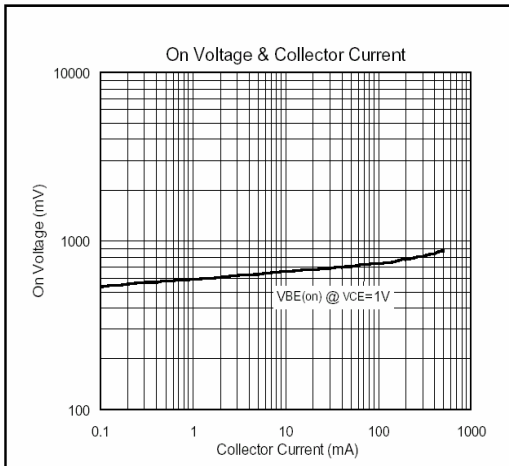
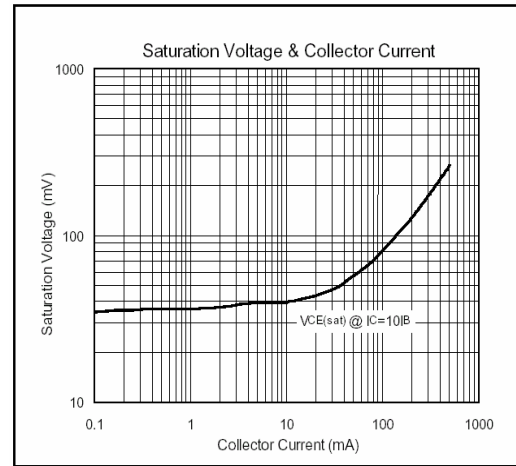
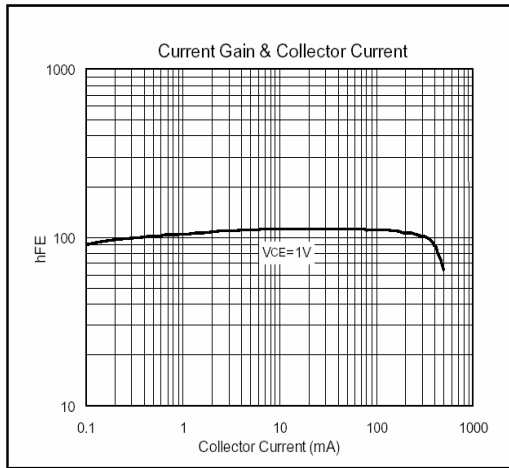
Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	T _j	+150	°C
Storage Temperature	T _{stg}	-55 ~ +150	°C
Collector to Base Voltage	VCBO	-80	V
Collector to Emitter Voltage	VCEO	-80	V
Emitter to Base Voltage	VEBO	-4	V
Collector Current	I _C	-500	mA
Total Power Dissipation	PD	225	mW

Characteristics at Ta = 25°C

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	-80	-	-	V	I _C =-100uA, I _E =0
BVCEO	-80	-	-	V	I _C =-1mA, I _B =0
BVEBO	-4	-	-	V	I _E =-100uA, I _C =0
ICBO	-	-	-100	nA	V _{CB} =-80V, I _E =0
ICEO	-	-	-100	nA	V _{CE} =-60V
VCE(sat)	-	-	-250	mV	I _C =-100mA, I _B =-10mA
VBE(on)	-	-	-1.2	V	V _{CE} =-1V, I _C =-100mA
HFE1	50	-	-		V _{CE} =-1V, I _C =-10mA
HFE2	50	-	-		V _{CE} =-1V, I _C =-100mA
f _T	100	-	-	MHz	V _{CE} =-2V, I _C =-10mA, f=1MHz

Characteristics Curve



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